

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

1. (Currently Amended) A laser beam mask for shaping a laser beam, comprising:
a base substrate having first and second surfaces and having at least one first open
portion; and
a reflecting layer on the first surface of the base substrate, wherein the reflecting layer has
at least one second open portion corresponding to the at least one first open portion and has a
refractive index and a thickness such that the reflecting layer totally reflects the laser beam.
2. (Original) The mask according to claim 1, wherein the laser beam is transmitted from
the base substrate to the reflecting layer.
3. (Original) The mask according to claim 1, wherein the reflecting layer includes a
dielectric material.
4. (Original) The mask according to claim 3, wherein the reflecting layer is formed
using a mirror coating method for selecting a refractive index of the dielectric material and
adjusting a thickness of the reflecting layer.

5. (Original) The mask according to claim 1, further comprising a first anti-reflecting layer formed on the second surface of the base substrate for minimizing reflectance of the laser beam.

6. (Original) The mask according to claim 5, wherein the first anti-reflecting layer has at least one third open portion corresponding to the at least one first open portion.

7. (Currently Amended) The mask according to claim 5, further comprising a second anti-reflective layer formed on the reflecting layer for ~~layer for~~ minimizing reflectance of the laser beam.

8. (Original) The mask according to claim 7, wherein the second anti-reflective layer has at least one fourth open portion corresponding to the at least one first open portion.

9. (Original) The mask according to claim 7, wherein the first and second anti-reflecting layers include an organic material.

10. (Original) The mask according to claim 1, wherein the at least one first open portion substantially has a shape of slit.

11. (Original) The mask according to claim 1, wherein the laser beam mask includes one of quartz, glass and silicon.

12. (Currently Amended) A laser beam mask for shaping a laser beam, comprising:
a base substrate having first and second surfaces; and
a reflecting layer on the first surface of the base substrate, wherein the reflecting layer has at least one first open portion and has a refractive index and a thickness such that the reflecting layer totally reflects the laser beam.

13. (Original) The mask according to claim 12, wherein the laser beam is transmitted from the base substrate to the reflecting layer.

14. (Original) The mask according to claim 12, wherein the reflecting layer includes a dielectric material.

15. (Original) The mask according to claim 14, wherein the reflecting layer is formed through a mirror coating method for selecting a refractive index of the dielectric material and adjusting a thickness of the reflecting layer.

16. (Original) The mask according to claim 12, further comprising a first anti-reflecting layer formed on the second surface of the base substrate for minimizing reflectance of the laser beam.

17. (Original) The mask according to claim 16, wherein the first anti-reflecting layer has at least one second open portion corresponding to the at least one first open portion.

18. (Original) The mask according to claim 16, further comprising a second anti-reflective layer formed on the reflecting layer for minimizing reflectance of the laser beam.

19. (Original) The mask according to claim 18, wherein the second anti-reflective layer has at least one third open portion corresponding to the at least one first open portion.

20. (Original) The mask according to claim 18, wherein the first and second anti-reflecting layers include an organic material.

21. (Original) The mask according to claim 12, wherein the at least one first open portion substantially has a shape of slit.

22. (Original) The mask according to claim 12, wherein the laser beam mask includes one of quartz, glass and silicon.

23. (Withdrawn) An apparatus for crystallization of an amorphous silicon thin film, comprising:

a laser beam source emitting a laser beam;

an attenuator adjusting an intensity of the laser beam;

a homogenizer adjusting uniformity of the laser beam;

a mask including:

a base substrate having first and second surfaces; and

a reflecting layer on the first surface of the base substrate, wherein the reflecting layer has at least one first open portion and totally reflects the laser beam; and
a translation stage which the amorphous silicon thin film is loaded on.

24. (Withdrawn) The apparatus according to claim 23, wherein the base substrate of the mask has at least one second open portion corresponding to the at least one first open portion.

25. (Withdrawn) The apparatus according to claim 23, wherein the reflecting layer includes a dielectric material.